



PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Haruo Sunakawa, et al.

Examiner: S. Mulpuri

Serial No.: 09/821,411

Art Unit: 2812

Filed: March 29, 2001

Docket: 14463

For: METHOD OF MANUFACTURING A
NITROGEN-BASED SEMICONDUCTOR
SUBSTRATE AND A SEMICONDUCTOR
ELEMENT BY USING THE SAME

Dated: September 23, 2002

Assistant Commissioner for Patents
Washington, D.C. 20231

RESPONSE

Sir:

In response to the Office Action dated May 22, 2002, applicants submit the following Amendment for entry in the above-identified application.

IN THE SPECIFICATION:

Please replace the paragraph beginning on Page 12, line 29 with the following:

As shown in Fig. 2B, a SiO₂ film 16 is deposited to a thickness of 200nm on the surface of the GaN film 15 and a protection film 17 is formed on the SiO₂ film 16. The illustrated protection film 17 is composed of a titanium (Ti) film of 50nm thick and a gold (Au) film of 0.4μm thick. After deposition of the protection film 17, a heat treatment is carried out at a temperature of 450°C for ten minutes within a hydrogen atmosphere.

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner of Patents and Trademarks, Washington, D.C. 20231 on September 23, 2002.

Dated: September 23, 2002


Mishelle Mustafa